

**TOSHIBA**

**2SA1315**

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

# 2SA1315

POWER AMPLIFIER APPLICATIONS.  
POWER SWITCHING APPLICATIONS.

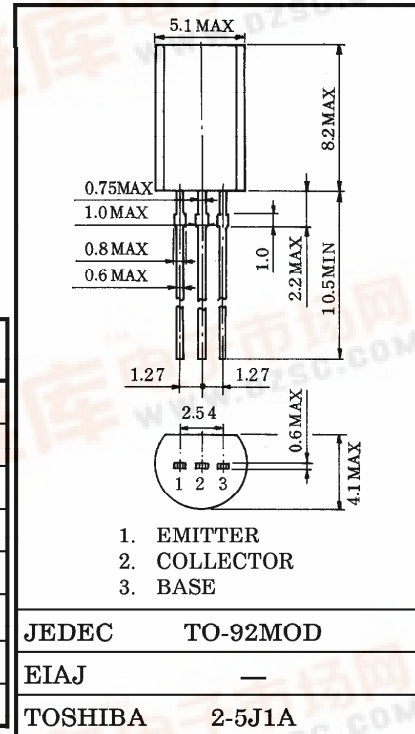
INDUSTRIAL APPLICATIONS

Unit in mm

- Low Collector Saturation Voltage  
:  $V_{CE(sat)} = -0.5V$  (Max.) ( $I_C = -1A$ )
- High Speed Switching Time :  $t_{stg} = 1.0\mu s$  (Typ.)
- Complementary to 2SC3328

MAXIMUM RATINGS ( $T_a = 25^\circ C$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	-80	V
Collector-Emitter Voltage	$V_{CEO}$	-80	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current	$I_C$	-2	A
Base Current	$I_B$	1	A
Collector Power Dissipation	$P_C$	900	mW
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature Range	$T_{stg}$	-55~150	$^\circ C$



Weight : 0.36g

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = -80V, I_E = 0$	—	—	-1.0	$\mu A$
Emitter Cut-off Current	$I_{EBO}$	$V_{EB} = -5V, I_C = 0$	—	—	-1.0	$\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-80	—	—	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE} = -2V, I_C = -0.5A$	70	—	240	
	$h_{FE(2)}$	$V_{CE} = -2V, I_C = -1.5A$	40	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -1A, I_B = -0.05A$	—	-0.2	-0.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -1A, I_B = -0.05A$	—	-0.9	-1.2	V
Transition Frequency	$f_T$	$V_{CE} = -2V, I_C = -0.5A$	—	80	—	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB} = -10V, I_E = 0, f = 1MHz$	—	45	—	pF
Switching Time	Turn-on Time	$t_{on}$		—	0.2	$\mu s$
	Storage Time	$t_{stg}$		—	1.0	
	Fall Time	$t_f$		—	0.2	

Note :  $h_{FE(1)}$  Classification    O : 70~140,    Y : 120~240

